

# BUK7510-100B

## N-channel TrenchMOS standard level FET

Rev. 03 — 14 April 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

### 1.4 Quick reference data

Table 1. Quick reference data

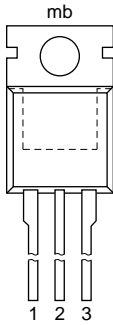
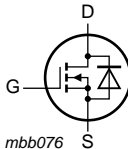
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ see <a href="#">Figure 1</a> ; see <a href="#">Figure 3</a>	[1]	-	75	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C};$ see <a href="#">Figure 2</a>	-	-	300	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $T_j = 25\text{ °C};$ see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	-	8.6	10	mΩ
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}; V_{sup} \leq 100\text{ V};$ $R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V};$ $T_{j(init)} = 25\text{ °C};$ unclamped	-	-	629	mJ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $V_{DS} = 80\text{ V}; T_j = 25\text{ °C};$ see <a href="#">Figure 13</a>	-	22	-	nC



[1] Continuous current is limited by package.

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78A (TO-220AB)**

## 3. Ordering information

**Table 3. Ordering information**

Type number	Package		Version
	Name	Description	
BUK7510-100B	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

## 4. Limiting values

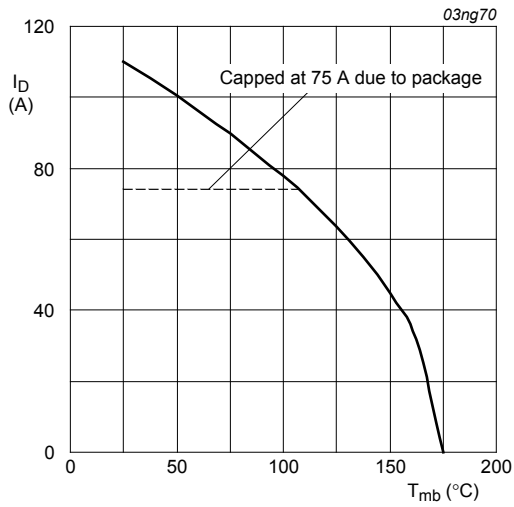
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	100	V	
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	-	100	V	
$V_{GS}$	gate-source voltage		-20	-	20	V	
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a> ; <a href="#">[1]</a> see <a href="#">Figure 3</a> <a href="#">[2]</a>	-	-	110	A	
			-	-	75	A	
		$T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a> <a href="#">[2]</a>	-	-	75	A	
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}$ ; $t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; see <a href="#">Figure 3</a>	-	-	438	A	
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	300	W	
$T_{stg}$	storage temperature		-55	-	175	°C	
$T_j$	junction temperature		-55	-	175	°C	
<b>Source-drain diode</b>							
$I_S$	source current	$T_{mb} = 25\text{ °C}$	<a href="#">[1]</a>	-	-	110	A
			<a href="#">[2]</a>	-	-	75	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$	-	-	438	A	
<b>Avalanche ruggedness</b>							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$ ; $V_{sup} \leq 100\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped	-	-	629	mJ	

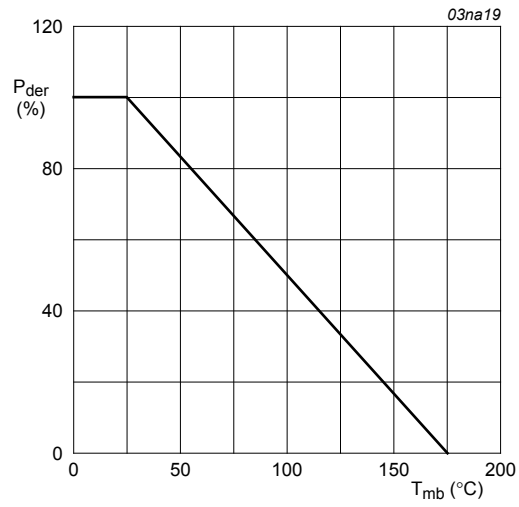
[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.



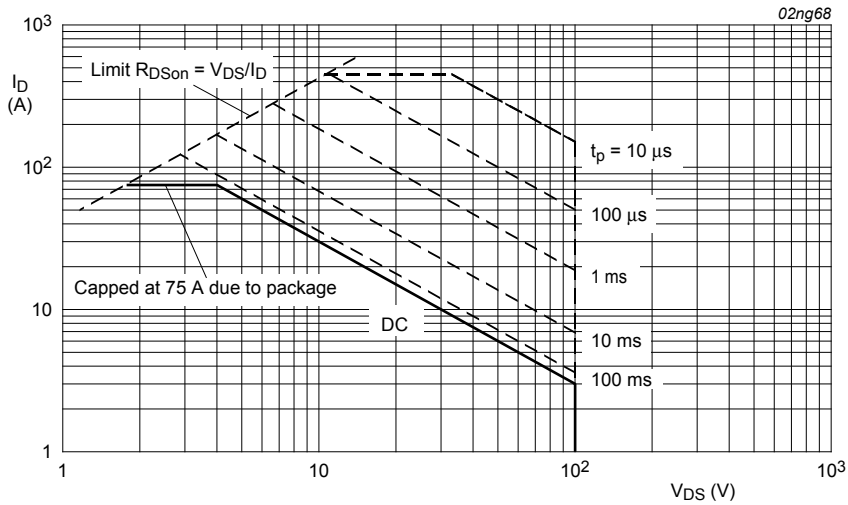
$$V_{GS} \geq 5 V$$

**Fig 1. Normalized continuous drain current as a function of mounting base temperature**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



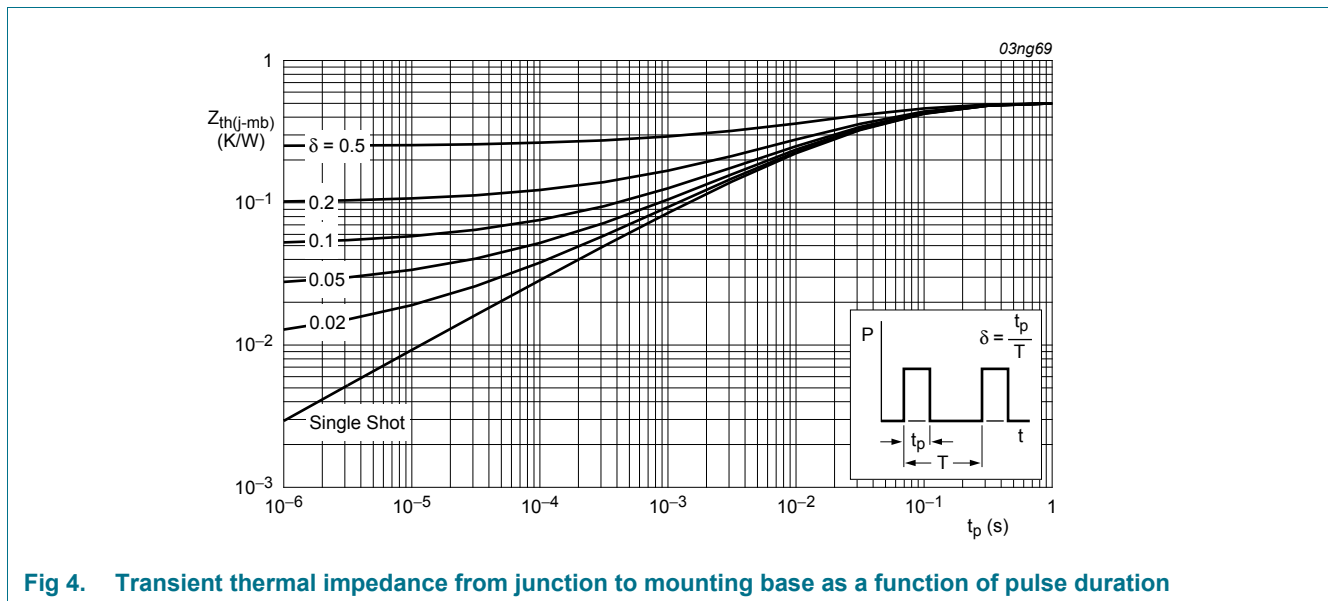
$$T_{mb} = 25^{\circ}C; I_{DM} \text{ is single pulse}$$

**Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	-	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

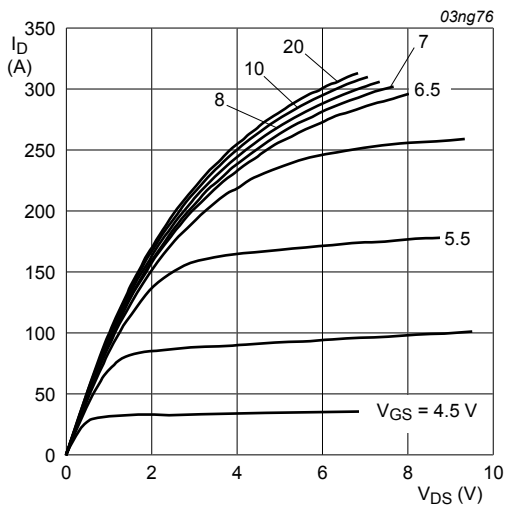


**Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 6. Characteristics

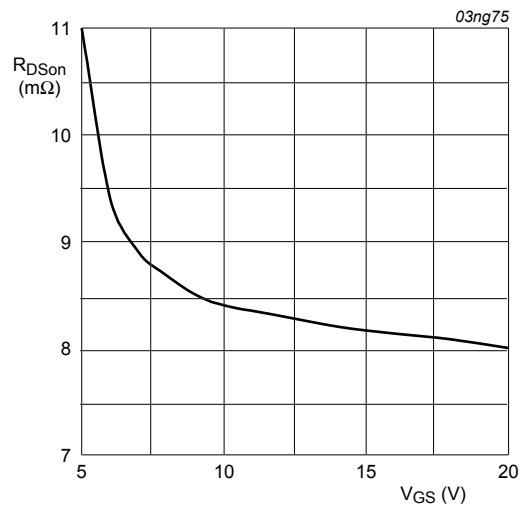
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	-	-	4.4	V
$I_{DSS}$	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	1	$\mu\text{A}$
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	-	-	25	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 11</a> ; see <a href="#">Figure 12</a>	-	8.6	10	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	80	-	nC
$Q_{GS}$	gate-source charge		-	18	-	nC
$Q_{GD}$	gate-drain charge		-	22	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 14</a>	-	5080	6773	pF
$C_{oss}$	output capacitance		-	677	812	pF
$C_{rss}$	reverse transfer capacitance		-	168	230	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 10 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	33	-	ns
$t_r$	rise time		-	45	-	ns
$t_{d(off)}$	turn-off delay time		-	120	-	ns
$t_f$	fall time		-	36	-	ns
$L_D$	internal drain inductance	from contact screw on mounting base to centre of die SOT78 ; $T_j = 25 \text{ }^\circ\text{C}$	-	3.5	-	nH
		from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	nH
$L_S$	internal source inductance	from source lead to source bond pad ; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	nH
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 15</a>	-	0.85	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s};$ $V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	69	-	ns
$Q_r$	recovered charge		-	212	-	nC



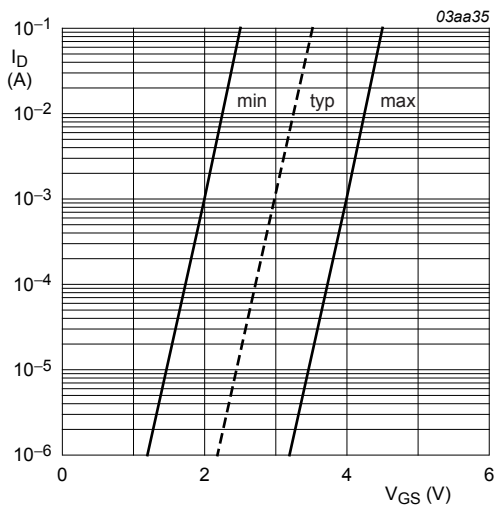
$T_j = 25^\circ\text{C}; t_p = 300\mu\text{s}$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values**



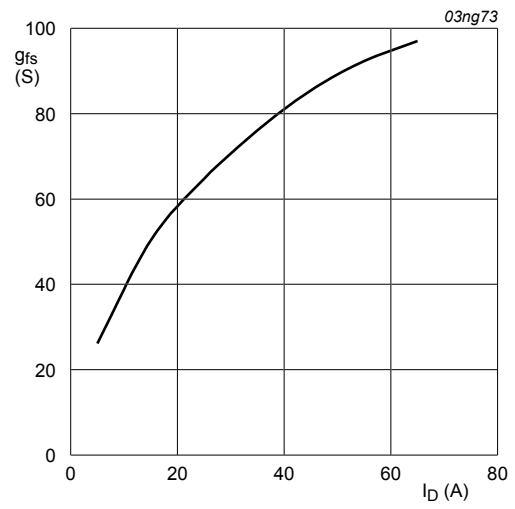
$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

**Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values**



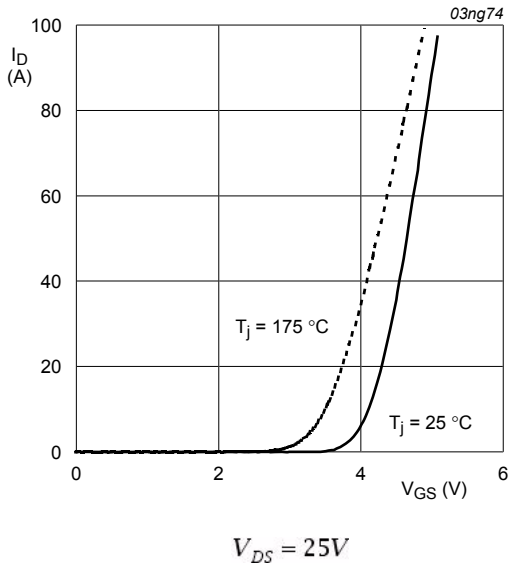
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

**Fig 7. Sub-threshold drain current as a function of gate-source voltage**

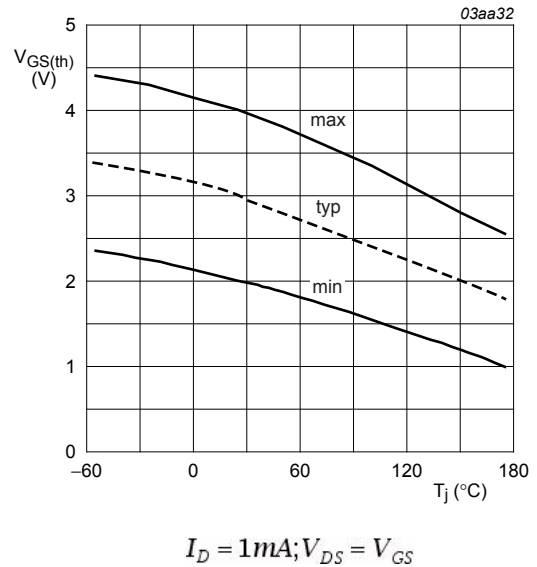


$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$

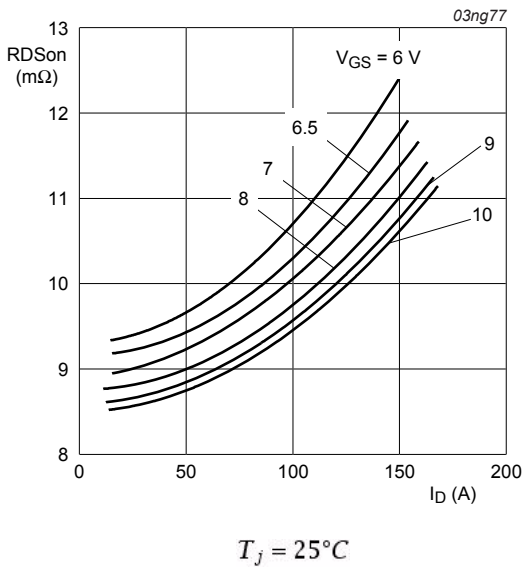
**Fig 8. Forward transconductance as a function of drain current; typical values**



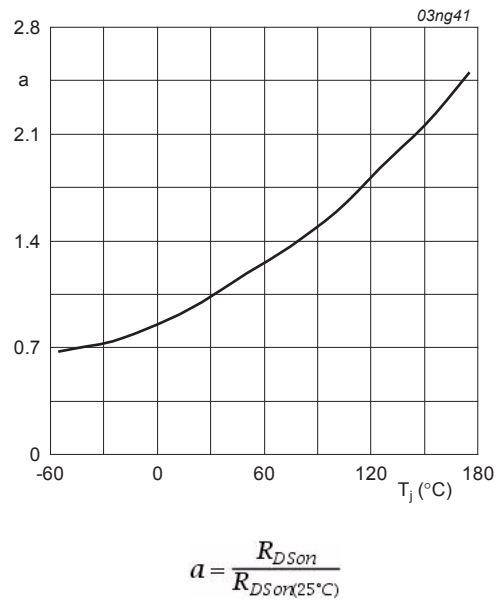
**Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



**Fig 10. Gate-source threshold voltage as a function of junction temperature**

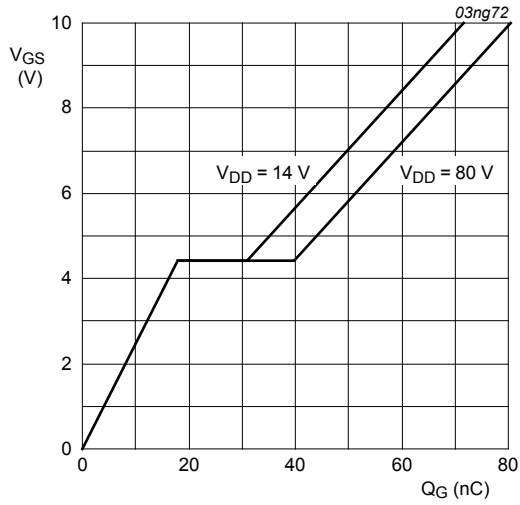


**Fig 11. Drain-source on-state resistance as a function of drain current; typical values**



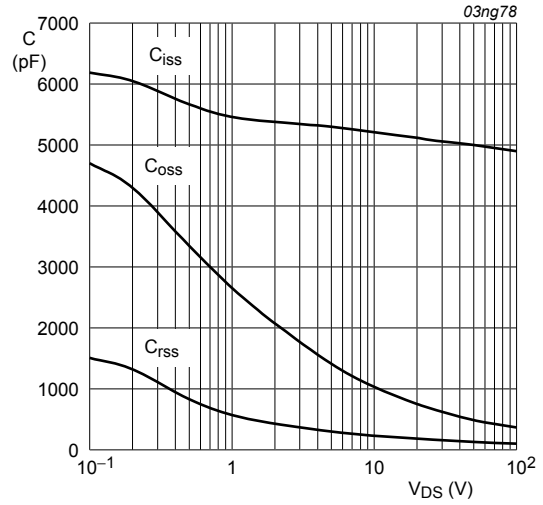
**Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature**





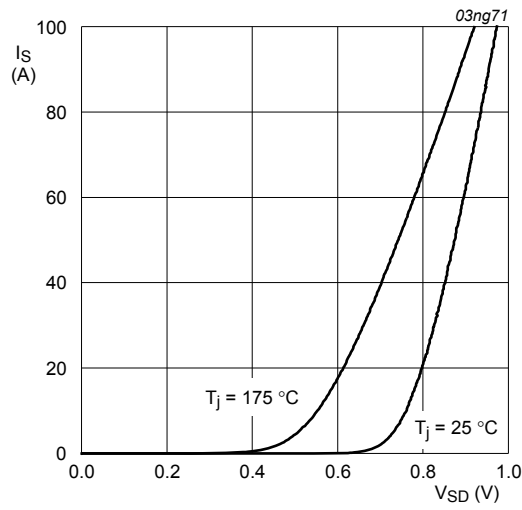
$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

**Fig 13. Gate-source voltage as a function of gate charge; typical values**



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

**Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



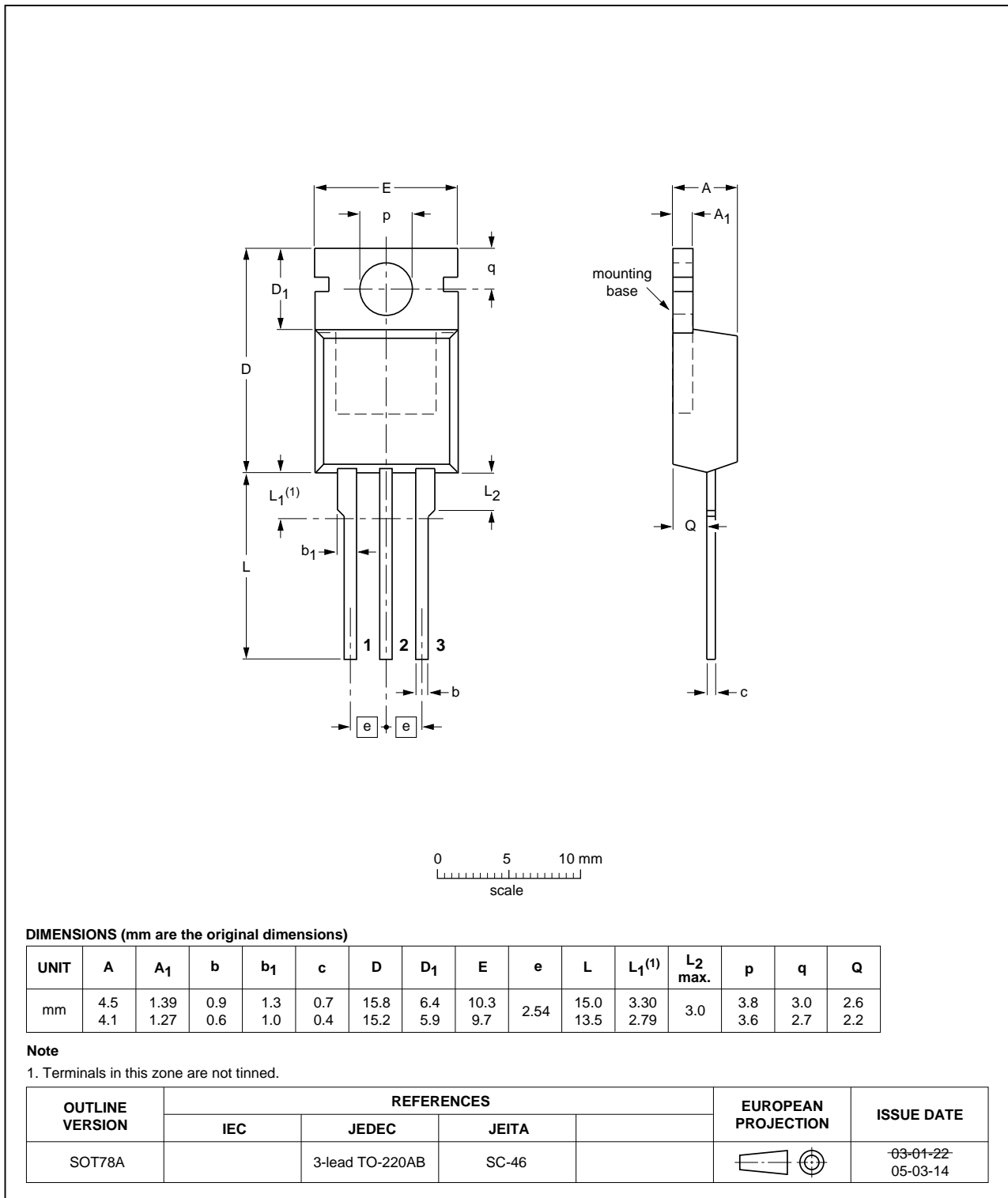
$V_{GS} = 0\text{V}$

**Fig 15. Reverse diode current as a function of reverse diode voltage; typical value**

**7. Package outline**

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A



**Fig 16. Package outline SOT78A (TO-220AB)**

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7510-100B_3	20100414	Product data sheet	-	BUK75/7610_100B_2 (9397 750 10281)
Modifications:				<ul style="list-style-type: none"><li>• BUK7510-100B_3 has been separated from data sheet BUK75/7610-100B_2.</li><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li></ul>
BUK75/7610_100B_2 (9397 750 10281)	20020919	Product data sheet	-	9397 750 09496

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

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